

In the specification:

Please add the following new paragraph after original paragraph beginning at page 7, line 12:

Fig. 14 is a section view showing a method of manufacturing a semiconductor device according to an embodiment of the present invention.

Please amend the paragraph beginning at page 13, line 5 as follows:

Although an example that the invention is applied to a semiconductor device having one side LDD construction (having low concentration drain region and high concentration drain region at only region side) in each of the above-mentioned embodiments is described, the invention may be applied to both side LDD construction (having low concentration drain region and high concentration drain region at both of source and drain sides). For example, Fig. 14 shows a device having a high concentration 5 source region formed in a low concentration source region 5A.